 Member of the Texas Instruments Widebus[™] Family 	DGG, DGV, OR (TOP \	
 EPIC[™] (Enhanced-Performance Implanted CMOS) Submicron Process 		56] CLK 55] 1A
Checks Parity	1Y2 3	54] 11A/YERREN
 Able to Cascade With a Second SN74ALVCH16903 	GND 4 2Y1 5	53 GND 52 11Y1
 Bus Hold on Data Inputs Eliminates the 	2Y2 🛛 6	51 🛛 11Y2
Need for External Pullup/Pulldown	V _{CC} [] 7	50 🛛 V _{CC}
Resistors	3Y1 🛿 8	49 🛛 2A
 Package Options Include Plastic 300-mil 	3Y2 🛛 9	48 🛛 3A
Shrink Small-Outline (DL), Thin Shrink	4Y1 🛛 10	47 🛛 4A
Small-Outline (DGG), and Thin Very	GND 11	46 🛛 GND
Small-Outline (DGV) Packages	4Y2 🛛 12	45 1 2A
	5Y1 🛛 13	44 1 2Y1
description	5Y2 🛛 14	43 1 2Y2
This 12-bit universal bus driver is designed for 3-V	6Y1 🛛 15	42 5 A
to 3.6-V V_{CC} operation.	6Y2 16	41 6A
	7Y1 17	40 7A
The SN74ALVCH16903 has dual outputs and can	GND 18	39 GND
operate as a buffer or an edge-triggered register.	7Y2 19	
In both modes, parity is checked on APAR, which	8Y1 20	37 8A
arrives one cycle after the data to which it applies.	8Y2 21	36 YERR
The YERR output, which is produced one cycle	V _{CC} 22	35 V _{CC}
after APAR, is open drain.	9Y1 23	
MODE selects one of the two data paths. When	9Y2 24	
MODE is low, the device operates as an		32 GND
edge-triggered register. On the positive transition	10Y1 🛛 26	31 🛛 10A

MODE is low, the device operates as an edge-triggered register. On the positive transition of the clock (CLK) input and when the clock-enable (CLKEN) input is low, data set up at the A inputs is stored in the internal registers. On the positive transition of CLK and when CLKEN is high, only data set up at the 9A–12A inputs is stored in their internal registers. When MODE is high, the device operates as a buffer and data at the A inputs passes directly to the outputs. 11A/YERREN serves a dual purpose; it acts as a normal data bit and also enables YERR data to be clocked into the YERR output register.

When used as a single device, parity output enable (PAROE) must be tied high; when parity input/output
(PARI/O) is low, even parity is selected and when PARI/O is high, odd parity is selected. When used in pairs
and PAROE is low, the parity sum is output on PARI/O for cascading to the second SN74ALVCH16903. When
used in pairs and PAROE is high, PARI/O accepts a partial parity sum from the first SN74ALVCH16903.

10Y2 27

28

PAROE

30 PARI/O

CLKEN

29



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PRODUCT PREVIEW

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description (continued)

A buffered output-enable (OE) input can be used to place the 24 outputs and YERR in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

OE does not affect the internal operation of the device. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, OE should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16903 is characterized for operation from 0°C to 70°C.

	FUNCTION								
	INPUTS					PUTS			
OE	MODE	CLKEN	CLK	Α	1Yn [†] -8Yn [†] 9Yn [†] -12Y				
L	L	L	Ŷ	Н	Н	Н			
L	L	L	\uparrow	L	L	L			
L	L	Н	\uparrow	Н	Y ₀	н			
L	L	Н	\uparrow	L	Y ₀	L			
L	н	L	Х	Н	н	н			
L	н	L	Х	L	L	L			
Н	Х	L	Х	Х	Z	Z			

Function Tables

† n =	1, 2
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PARITY FUNCTION

		INP	UTS			
OE	PAROE [‡]	11A/YERREN§	PARI/O	Σ OF INPUTS 1A – 10A = H	APAR	OUTPUT YERR
L	Н	L	L	0, 2, 4, 6, 8, 10	L	Н
L	Н	L	L	1, 3, 5, 7, 9	L	L
L	Н	L	L	0, 2, 4, 6, 8, 10	Н	L
L	Н	L	L	1, 3, 5, 7, 9	Н	Н
L	Н	L	Н	0, 2, 4, 6, 8, 10	L	L
L	Н	L	Н	1, 3, 5, 7, 9	L	н
L	Н	L	Н	0, 2, 4, 6, 8, 10	Н	н
L	Н	L	Н	1, 3, 5, 7, 9	Н	L
Н	Х	Х	Х	Х	Х	Н
L	Х	Н	Х	Х	Х	Н

[‡]When used as a single device, PAROE must be tied high.

§ Valid after appropriate number of clock pulses have set internal register



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC}	–0.5 V to 4.6 V
Input voltage range, V _I (see Note 1)	–0.5 V to 4.6 V
Output voltage range, V _O (see Notes 1 and 2)	–0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I_{OK} (V _O < 0 or V _O > V _{CC})	±50 mA
Continuous output current, $I_O (V_O = 0 \text{ to } V_{CC})$	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package	
DGV package	
DL package	
Storage temperature range, T _{stg}	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

- 2. This value is limited to 4.6 V maximum.
- 3. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.



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recommended operating conditions (see Note 4)

VCC	V _{CC} Supply voltage						
VIH	High-level input voltage	$V_{CC} = 3 V to$	3.6 V	2		V	
VIL	Low-level input voltage	$V_{CC} = 3 V to$	3.6 V		0.8	V	
VI	Input voltage			0	VCC	V	
VO	V _O Output voltage						
	High-level output current		PARI/O		-12	mA	
ЮН		V _{CC} = 3 V	Y port		-24	ША	
			PARI/O		12		
IOL	Low-level output current	$V_{CC} = 3 V$	Y port		24	mA	
		YERR output					
$\Delta t / \Delta v$ Input transition rise or fall rate						ns/V	
Τ _Α	Operating free-air temperature			0	70	°C	

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER	TEST C	ONDITIONS	Vcc	MIN	TYP†	MAX	UNIT
		I _{OH} = -100 μA		3 V to 3.6 V	V _{CC} -0.2			
Vari	Y port	I _{OH} = -12 mA,	VIH = 2 V	3 V	2.4			v
VOH		I _{OH} = -24 mA,	VIH = 2 V	3 V	2			v
	PARI/O	I _{OH} = -12 mA,	VIH = 2 V	3 V	2			
	Viport	I _{OL} = 100 μA		3 V to 3.6 V			0.2	
V.	Y port	I _{OL} = 24 mA,	V _{IL} = 0.8 V	3 V			0.55	v
VOL	PARI/O	I _{OL} = 12 mA,	V _{IL} = 0.8 V	3 V			0.55	v
	YERR output	I _{OL} = 24 mA		3 V			0.5	
l		V _I = V _{CC} or GND		3.6 V			±5	μA
		VI = 0.8 V		3 V	75			μA
ll(hold)		VI = 2 V		3.	-75			
		V _I = 0 to 3.6 V [‡]		3.6 V			±500	
ЮН	YERR output	AO = ACC		0 to 3.6 V			±10	μA
loz§		$V_{O} = V_{CC}$ or GND		3.6 V			±10	μA
ICC		V _I = V _{CC} or GND,	I ^O = 0	3.6 V			40	μA
∆ICC		One input at V _{CC} –0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μA
0.	Control inputs			3.3 V				~F
Ci	Data inputs	$V_{I} = V_{CC}$ or GND		3.3 V				pF
<u> </u>	YERR output			3.3 V				~ [
Co	Data outputs	$V_{O} = V_{CC}$ or GND		3.3 V				pF
Cio	PARI/O	V _O = V _{CC} or GND		3.3 V				pF

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25° C.

[‡]This is the bus-hold maximum dynamic current required to switch the input from one state to another.

For I/O ports, the parameter I_{OZ} includes the input leakage current.



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timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

				V _{CC} = 2.5 V ± 0.2 V		V _{CC} =	2.7 V	V _{CC} = 3.3 V ± 0.3 V		UNIT	
				MIN	MAX	MIN	MAX	MIN	MAX		
fclock	Clock frequency									MHz	
tw	Pulse duration, CLK	↑								ns	
		1A–12A before CLK [↑]	Register mode								
		1A–10A before CLK [↑]	Buffer mode								
			Register mode								
t _{su}	Setup time	APAR before CLK↑	Buffer mode					ns			
		PARI/O before CLK↑	Both modes								
		11A/YERREN before CLK↑	Buffer mode								
		CLKEN before CLK↑	Register mode								
		1A–12A after CLK [↑]	Register mode								
		1A–10A after CLK↑	Buffer mode								
			Register mode								
L.	Hold time	APAR after CLK↑	Buffer mode								
th	Hold lime		Register mode						r	ns	
	PARI/O after CLK↑	Buffer mode									
		11A/YERREN after CLK↑	Buffer mode								
		CLKEN after CLK [↑]	Register mode								

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PA	RAMETER	FROM	ROM TO NPUT) (OUTPUT)	V _{CC} = 2.5 V ± 0.2 V	V _{CC} = 2.7 V	V _{CC} = 3.3 V ± 0.3 V	UNIT
		(INFOT)	(001701)	MIN MAX	MIN MAX	MIN MAX	
fmax							MHz
	Buffer mode	А	Y				
L .		s CLK	YERR				ns
^t pd	Both modes		PARI/O				
		MODE	Y				ns
tpd [†]	Both modes	CLK	PARI/O				ns
^t PLH	Register mode	CLK	Y				20
^t PHL	Register mode		CLK Y				ns
	Dette me des	OE	Y				
ten	Both modes	PAROE	PARI/O				ns
		OE	Y				
tdis	Both modes	PAROE	PARI/O				ns
^t PLH	Dath madea	ŌĒ	YERR				
^t PHL	Both modes	UE	TERR				ns

[†] The load for this parameter has been specified by Hewlett-Packard Company. This parameter is warranted but not production tested.



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simultaneous switching characteristics over recommended operating free-air temperature range, C_L = 50 pF and R_L = 10 Ω (unless otherwise noted) (see Figure 2)[†]

PAF	RAMETER	FROM TO (INPUT) (OUTPUT)		= ۷ _{CC} ± 0.2		V _{CC} =	2.7 V	= V _{CC} ± 0.3	3.3 V 3 V	UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
^t PLH [‡]	Pogiator modo	CLK	V							
^t PHL [‡]	Register mode	ULK	ľ							ns

[†] All outputs switching

[‡] This parameter is warranted but not production tested.

operating characteristics, $T_A = 25^{\circ}C$

	PARAMETER	TEST CO	ONDITIONS	V _{CC} = 2.5 V ± 0.2 V TYP	V _{CC} = 3.3 V ± 0.3 V TYP	UNIT	
	Power dissipation capacitance	Outputs enabled	$c_1 = 0$	f = 10 MHz			рF
Cpd	Power dissipation capacitance	Outputs disabled	C _L = 0,				рг





- - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r \leq 2.5 ns, t_f \leq 2.5 ns. D. The outputs are measured one at a time with one transition per measurement.

 - E. tpLz and tpHz are the same as tdis.
 - F. t_{PZL} and t_{PZH} are the same as t_{en} . G. tpLH and tpHL are the same as tpd.
 - H. t_{PHL} is measured at 1.5 V.
 - I. tpLH is measured at VOL + 0.3 V.





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PARAMETER MEASUREMENT INFORMATION V_{CC} = 3.3 V \pm 0.3 V



NOTES: A. $C_{\mbox{L}}$ includes probe and jig capacitance.

- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r \leq 2.5 ns, t_f \leq 2.5 ns.
- C. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 2. Load Circuit and Voltage Waveforms



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